

IN THE SPECIFICATION

Please amend the Specification as follows:

From the preliminary amendment filed on 12/12/2003, please amend the new section heading and paragraph added on page 2 as follows:

"CROSS-REFERENCE TO RELATED APPLICATION

This non-provisional United States (U.S.) patent application claims the benefit [[of]] and is a divisional application of U.S. Patent Application No. 10/119,594 filed on April 04, 2002 by inventors Alexander Kalnitsky et al., entitled "SELF-ALIGNED NPN TRANSISTOR WITH RAISED EXTRINSIC BASE", now U.S. Pat. No. 6,767,798, ~~which are both of which~~ are assigned to Maxim Integrated Products, Inc."

Paragraph number 0029, please replace the paragraph thereat with the amended paragraph as follows:

"Figure 3E illustrates a cross-sectional view of the exemplary semiconductor device 100 at another subsequent step of the exemplary method of forming a bipolar transistor in accordance with the invention. In this subsequent step, a thin nitride spacer 132 adjacent to the polysilicon emitter 130 is formed by depositing a layer of silicon nitride 134 having a thickness in the range of 0.01 microns to 0.1 microns and ~~isotropic~~ anisotropic etching the layers of silicon nitride 134. In the exemplary method, the silicon nitride layers 120, 134 are directionally etched with a plasma etcher."